

MOSFET – N-Channel, POWERTRENCH®

80 V, 50 A, 13.4 mΩ

FDMS86380-F085

Features

- Typ $R_{DS(on)}$ = 11.3 mΩ at $V_{GS} = 10\text{ V}$; $I_D = 50\text{ A}$
- Typ $Q_{g(tot)}$ = 20 nC at $V_{GS} = 10\text{ V}$; $I_D = 50\text{ A}$
- UIS Capability
- AEC-Q101 Qualified and PPAP Capable
- This Device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

Applications

- Automotive Engine Control
- PowerTrain Management
- Solenoid and Motor Drivers
- Electronic Steering
- Integrated Starter/Alternator
- Distributed Power Architectures and VRM
- Primary Switch for 12 V Systems

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

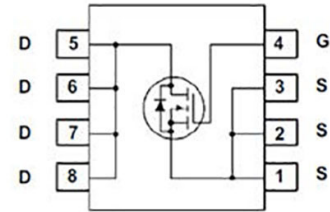
Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSS}	80	V	
Gate-to-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current ($V_{GS} = 10\text{ V}$) (Note 1)	I_D	$T_C = 25^\circ\text{C}$	50	A
Pulsed Drain Current		$T_C = 25^\circ\text{C}$	See Figure 4	
Single Pulse Avalanche Energy (Note 2)	E_{AS}	16	mJ	
Power Dissipation	P_D		75	W
Derate above 25°C			0.5	W/ $^\circ\text{C}$
Operating and Storage Temperature	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$	
Thermal Resistance (Junction-to-Case)	$R_{\theta JC}$	2	$^\circ\text{C}/\text{W}$	
Maximum Thermal Resistance (Junction-to-Ambient) (Note 3)	$R_{\theta JA}$	50	$^\circ\text{C}/\text{W}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

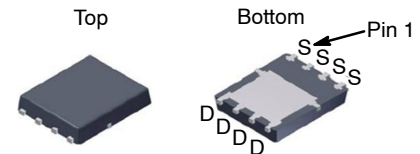
1. Current is limited by bondwire configuration.
2. Starting $T_J = 25^\circ\text{C}$, $L = 20\ \mu\text{H}$, $I_{AS} = 40\text{ A}$, $V_{DD} = 80\text{ V}$ during inductor charging and $V_{DD} = 0\text{ V}$ during time in avalanche.
3. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2 oz copper.

$V_{(BR)DSS}$	$R_{DS(ON)}\text{ MAX}$	$I_D\text{ MAX}$
80 V	13.4 mΩ @ 10 V	50 A

ELECTRICAL CONNECTION

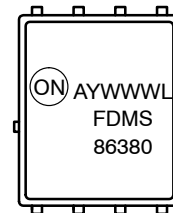


N-Channel MOSFET



PQFN8
CASE 483BJ

MARKING DIAGRAM



A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
FDMS86380 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
FDMS86380-F085	PQFN8 (Power 56) (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

FDMS86380-F085

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

B_{VDSS}	Drain-to-Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}$	80	-	-	V	
I_{DSS}	Drain-to-Source Leakage Current	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$	-	-	1	μA
			$T_J = 175^\circ\text{C}$ (Note 4)	-	-	1	mA
I_{GSS}	Gate-to-Source Leakage Current	$V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	

ON CHARACTERISTICS

$V_{GS(th)}$	Gate-to-Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	2.0	3.0	4.0	V	
$R_{DS(on)}$	Drain-to-Source On-Resistance	$I_D = 50 \text{ A}, V_{GS} = 10 \text{ V}$	$T_J = 25^\circ\text{C}$	-	11.3	13.4	$\text{m}\Omega$
			$T_J = 175^\circ\text{C}$ (Note 4)	-	25.3	30.0	

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	1440	-	pF	
C_{oss}	Output Capacitance		-	300	-		
C_{riss}	Reverse Transfer Capacitance		-	14	-		
R_g	Gate Resistance	$f = 1 \text{ MHz}$	-	2.0	-	Ω	
$Q_{g(tot)}$	Total Gate Charge	$V_{GS} = 0 \text{ to } 10 \text{ V}$	$V_{DD} = 64 \text{ V}, I_D = 50 \text{ A}$	-	20	30	nC
$Q_{g(th)}$	Threshold Gate Charge	$V_{GS} = 0 \text{ to } 2 \text{ V}$		-	2.7	-	
Q_{gs}	Gate-to-Source Gate Charge			-	8.8	-	
Q_{gd}	Gate-to-Drain "Miller" Charge			-	4.4	-	

SWITCHING CHARACTERISTICS

t_{on}	Turn-On Time	$V_{DD} = 40 \text{ V}, I_D = 50 \text{ A}, V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$	-	-	31	ns
$t_{d(on)}$	Turn-On Delay		-	13	-	
t_r	Rise Time		-	8	-	
$t_{d(off)}$	Turn-Off Delay		-	15	-	
t_f	Fall Time		-	5	-	
t_{off}	Turn-Off Time		-	-	30	

DRAIN-SOURCE DIODE CHARACTERISTICS

V_{SD}	Source-to-Drain Diode Voltage	$I_{SD} = 50 \text{ A}, V_{GS} = 0 \text{ V}$	-	-	1.25	V
		$I_{SD} = 25 \text{ A}, V_{GS} = 0 \text{ V}$	-	-	1.2	
t_{rr}	Reverse Recovery Time	$I_F = 50 \text{ A}, dI_{SD}/dt = 100 \text{ A}/\mu\text{s}, V_{DD} = 64 \text{ V}$	-	37	55	ns
Q_{rr}	Reverse Recovery Charge		-	23	35	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The maximum value is specified by design at $T_J = 175^\circ\text{C}$. Product is not tested to this condition in production

TYPICAL CHARACTERISTICS

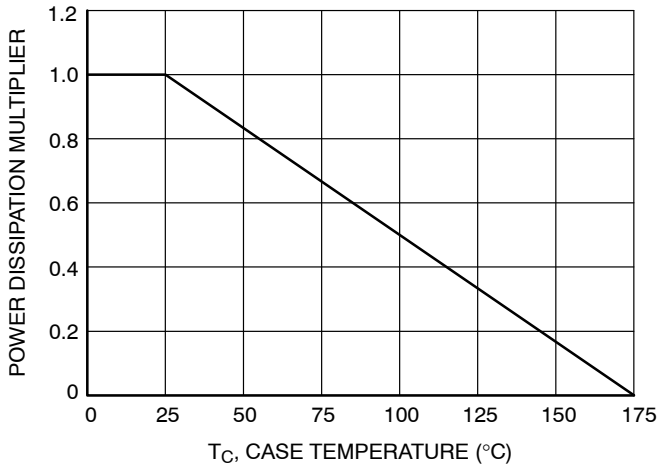


Figure 1. Normalized Power Dissipation vs. Case Temperature

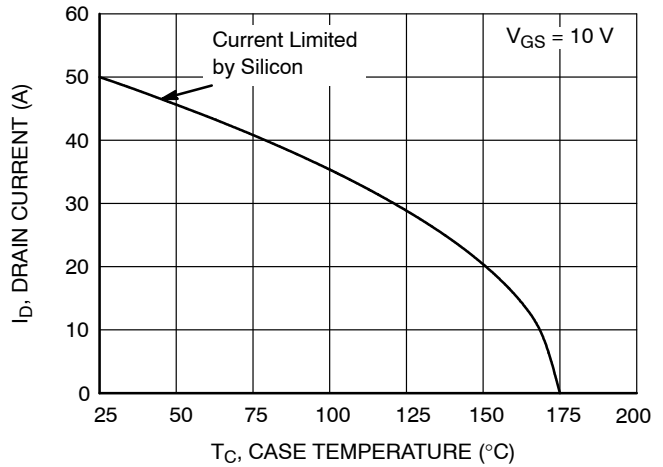


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

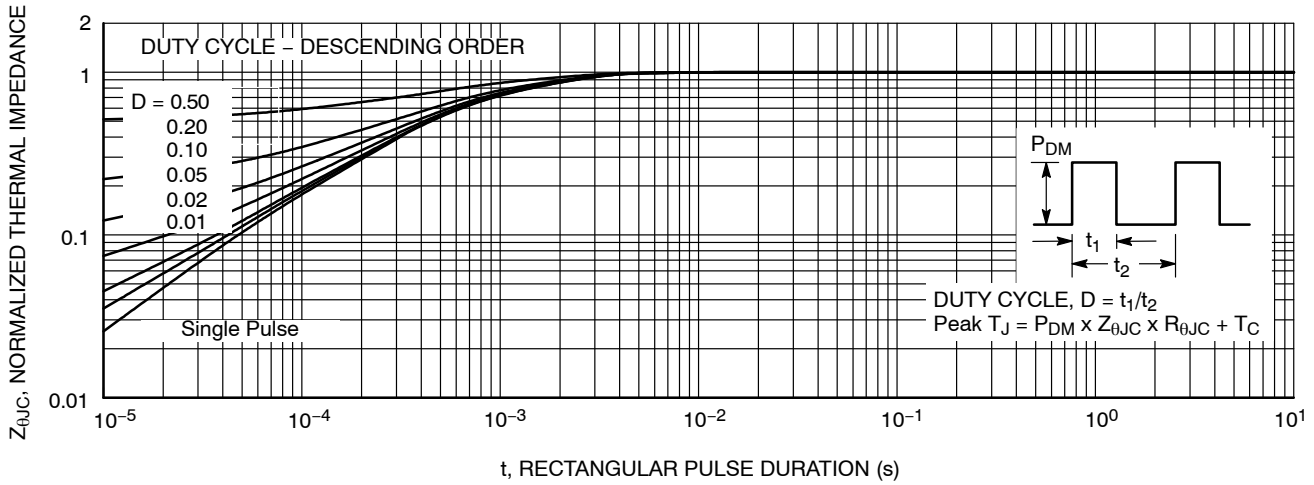


Figure 3. Normalized Maximum Transient Thermal Impedance

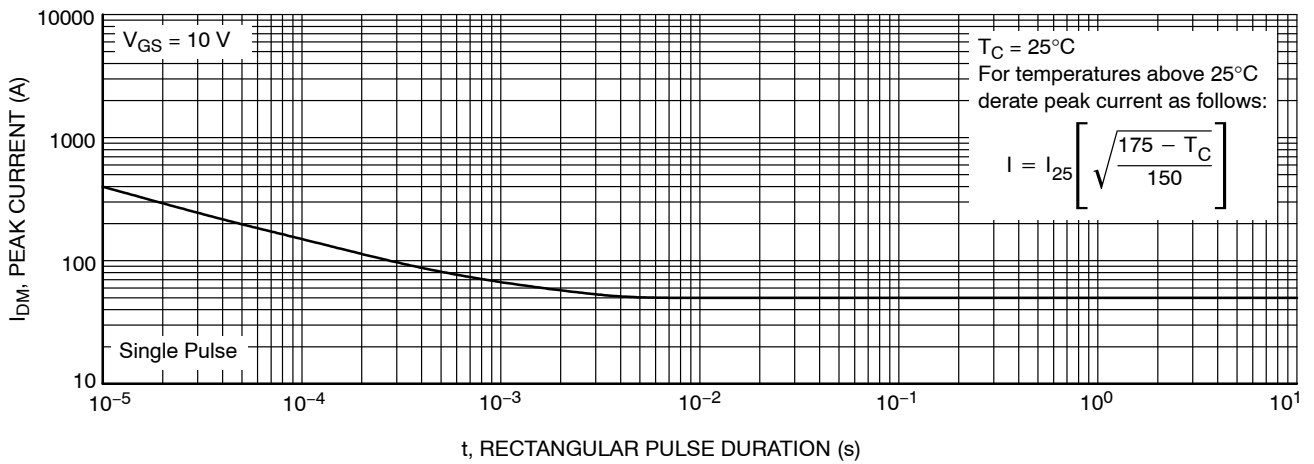


Figure 4. Peak Current Capability

TYPICAL CHARACTERISTICS (continued)

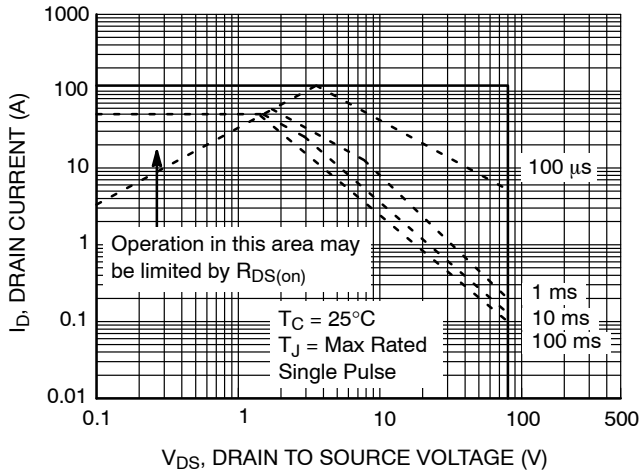
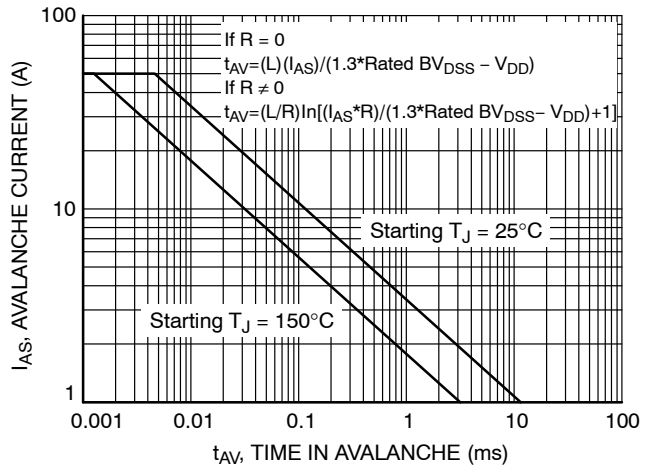


Figure 5. Forward Bias Safe Operating Area



(Note: Refer to onsemi Applications Notes [AN7514](#) and [AN7515](#))

Figure 6. Unclamped Inductive Switching Capability

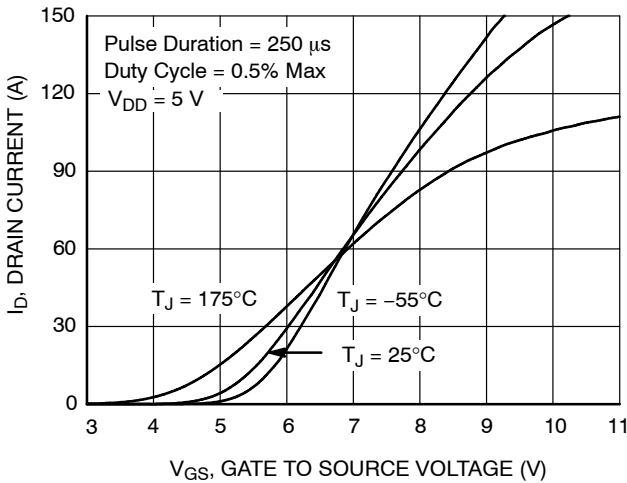


Figure 7. Transfer Characteristics

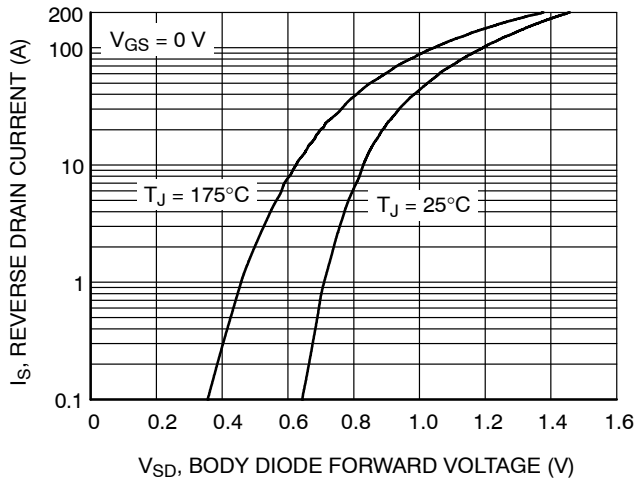


Figure 8. Forward Diode Characteristics

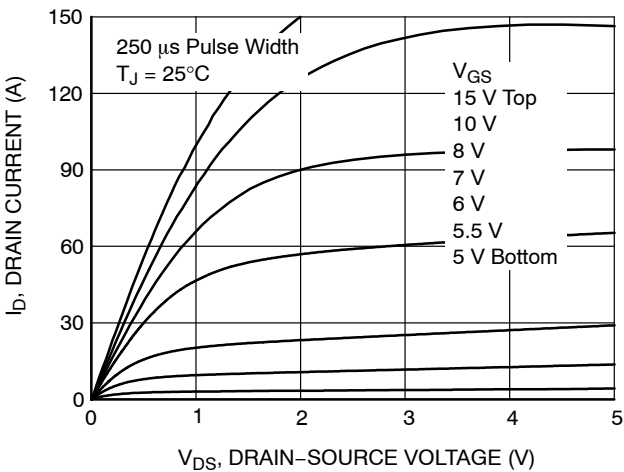


Figure 9. Saturation Characteristics

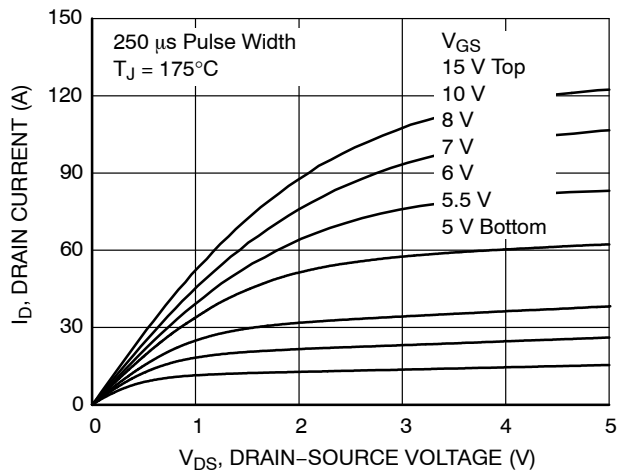


Figure 10. Saturation Characteristics

TYPICAL CHARACTERISTICS (continued)

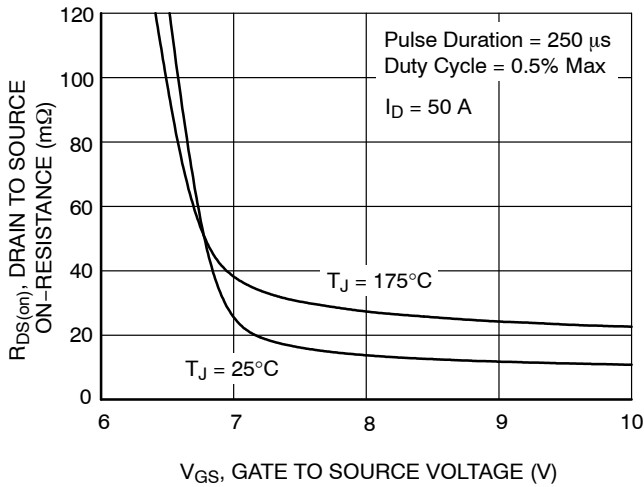


Figure 11. $R_{DS(on)}$ vs. Gate Voltage

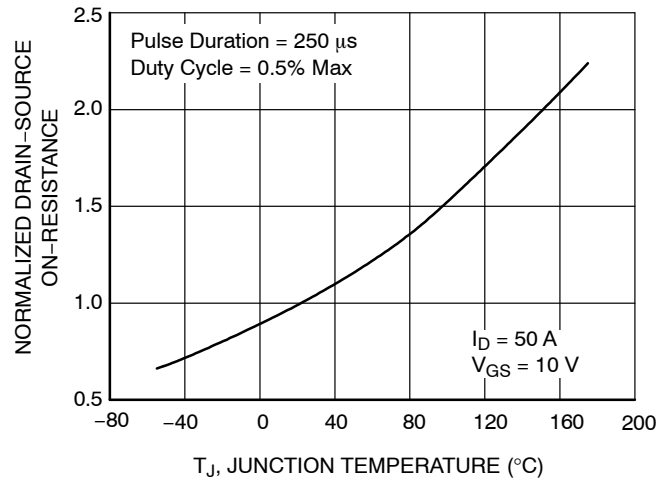


Figure 12. Normalized $R_{DS(on)}$ vs. Junction Temperature

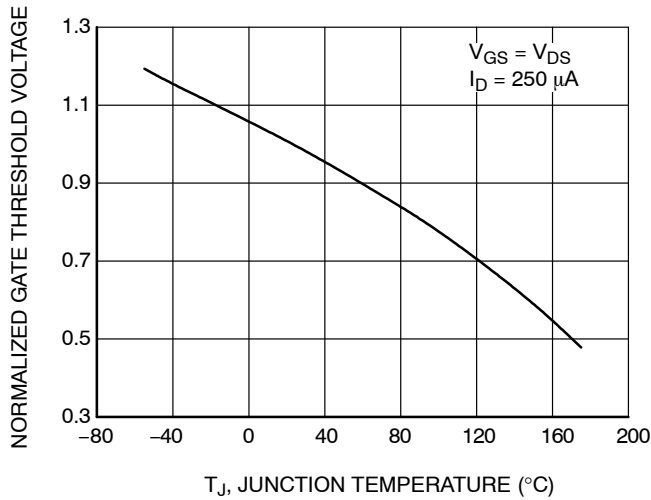


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

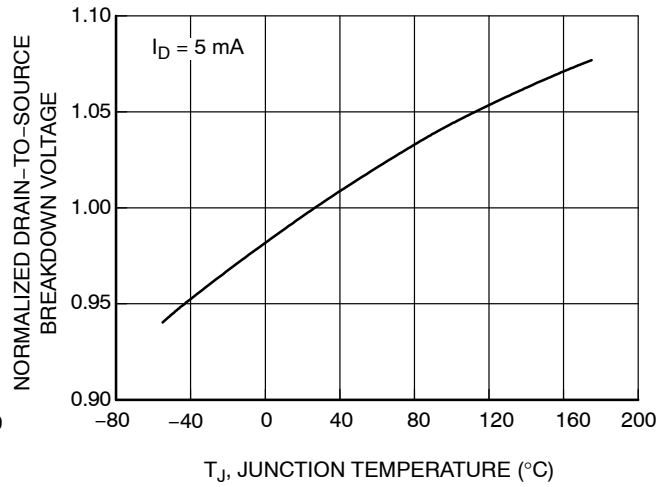


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

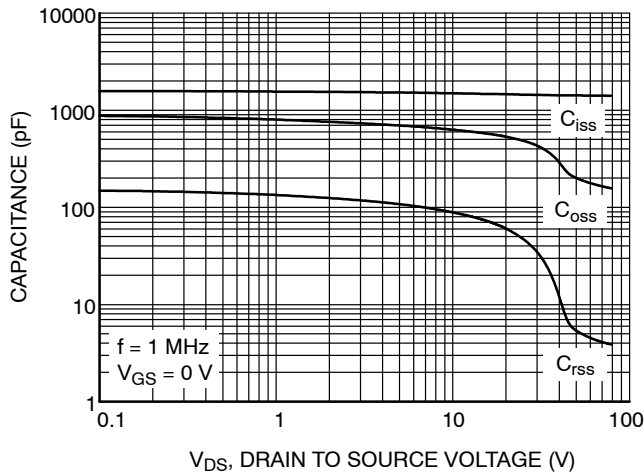


Figure 15. Capacitance vs. Drain to Source Voltage

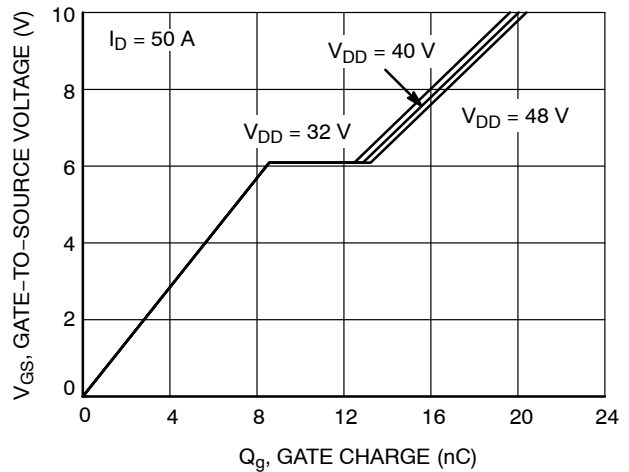


Figure 16. Gate Charge vs. Gate to Source Voltage

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®

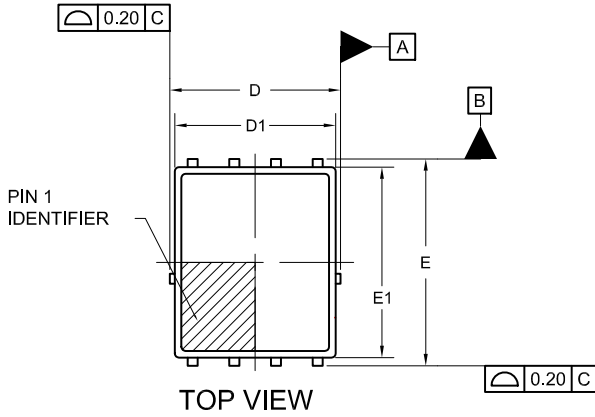


PQFN8 5X6, 1.27P

CASE 483BJ

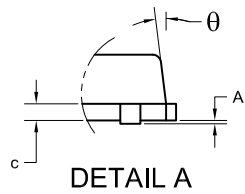
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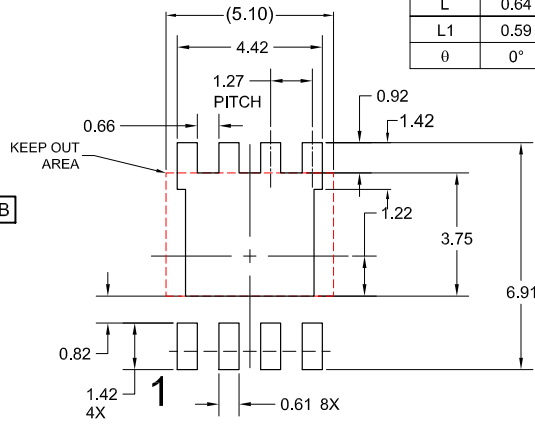
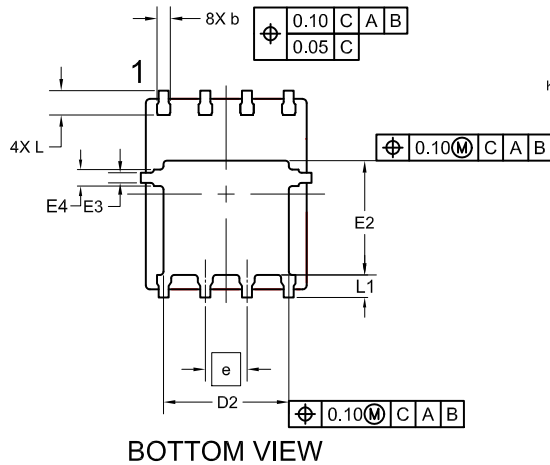
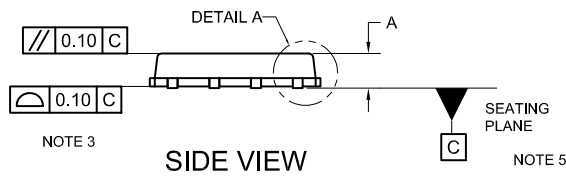


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. A1 IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	0.025	0.05
b	0.31	0.41	0.51
c	0.23	0.28	0.33
D	4.90	5.00	5.10
D1	4.80	4.90	5.00
D2	3.72	3.82	3.92
E	6.20	6.30	6.40
E1	5.70	5.80	5.90
E2	3.38	3.48	3.58
E3	0.30		
E4	0.50		
e	1.27 BSC		
L	0.64	0.74	0.84
L1	0.59	0.69	0.79
θ	0°	—	12°



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